

五、著作目錄(建議呈現有利於計畫審查之著作目錄，頁數以 2 頁為限)：

專書

[B.1] Yung C. Liang, Ganesh S. Samudra, Chih-Fang Huang, Power Microelectronics: Device and Process Technologies 2nd Ed., Singapore, World Scientific, 2017. ISBN: 978-981-3200-24-1

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[J.1] Jia-Wei Hu; Jheng-Yi Jiang; Wei-Chen Chen; Chih-Fang Huang*; Tian-Li Wu*; Kung-Yen Lee; Bing-Yue Tsui, "1100 V, 22.9 mΩ cm² 4H-SiC RESURF Lateral Double-Implanted MOSFET With Trench Isolation," *IEEE Transactions on Electron Devices*, vol. 68, no.10, pp. 5009-5013, Aug. 2021. MOST 109-2218-E-007-035. 通訊作者. (IF=2.917)

[J.2] Jheng-Yi Jiang, Chen-Xuan Tu, Jia-Wei Hu, Der-Sheng Chao, and Chih-Fang Huang*, "3.3 kV Class 4H-SiC Double-Implanted MOSFET with Excellent Radiation Hardness Against Gamma Rays using Counter-Doped Junction Termination Extension," *IEEE Electron Device Letters*, vol. 42, no. 5, pp. 727-730, May 2021. MOST 107-2923-E-007-008-MY2 通訊作者 (IF=4.187)

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- [C.2]J.-W. Hu, J.-Y. Jiang, P.-W. Huang, S.-W. Tang, Z.-H. Huang, T.-L. Wu, C.-F. Huang, and K.-Y. Lee (2021, Jun). 1.2 kV 4H-SiC VDMOSFETs with Siimplanted Surface: Performance Enhancement and Reliability Evaluation. The 33rd International Symposium on Power Semiconductor Devices and ICs (ISPSD 2021), Nagoya, Japan (Virtual). MOST 109-2218-E-007-035.
- [C.3]Chih-Yao Chang, Kuan-Ju Wu, Ching-Yao Wang, Yao-Luen Shen, Chun-Ta Hsu, Tian-Li Wu, and Chih-Fang Huang, “The Characteristics of Light Emitting HEMT with Single Quantum Well Inserted,” *2020 International Conference on Solid State Devices and Materials*, Japan, Sep. 2020. MOST 104-2221-E007-079.
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- [C.8]Jheng-Yi Jiang, Jia-Qing Hung, Pin-Wei Huang, Tian-Li Wu, and Chih-Fang Huang, “Study on the Effects of Si Implantation on the Interface of 4H-SiC MOSFET,” *2019 International Conference on Solid State Devices and Materials*, Nagoya, Japan, Sep. 2019. MOST 107-2218-E-007-042.
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